

## PATENT APPLICATION

FORM PTO-1449

ATTY. DOCKET NO.

SERIAL NO.

10991002-4

APPLICANT

Tetsuya Takeuchi et al.

FILING DATE

GROUP

Herewith

(Use several sheets if necessary)



## REFERENCE DESIGNATION

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	AF	EP0723303A	07/24/96	EP		
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EXAMINER  
Rev 5/90 (Form 3.05)

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APPLICANT

Tetsuya Takeuchi et al.

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Dec. 19, 2001

GROUP

MAR 04 2002

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME
1A			
1B			
1C			
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## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	NAME	TRANSLATION	
				YES	NO
DW	1L WO 99/25030	05/20/99	PCT		
DW	1M 09-199759	07/31/97	Japan	X	
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DW	1Q	Usui, Akira et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Japan Journal of Applied Physics, Vol. 36, 1997, pp. L899-902.
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